TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N - CHANNEL MOS TYPE

# GT80J101

#### HIGH POWER SWITCHING APPLICATIONS.

High Input Impedance

High Speed :  $t_f = 0.40 \mu s \, (Max.)$ 

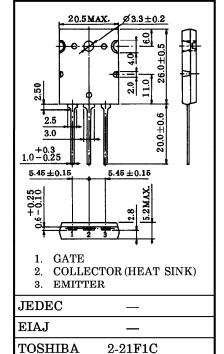
Low Saturation Voltage :  $V_{CE(sat)}=3.5V$  (Max.)

Enhancement-Mode

#### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		VCES	600	V
Gate-Emitter Voltage		$v_{GES}$	±20	V
Collector Current	DC	$I_{\mathbf{C}}$	80	Α
	1ms	$I_{CP}$	160	] A
Collector Power Dissipation (Tc=25°C)		PC	200	w
Junction Temperature		$T_{j}$	150	°C
Storage Temperature Range		${ m T_{stg}}$	-55~150	°C
Screw Torque		_	0.8	$N \cdot m$

## Unit in mm



Weight: 9.75g

### ELECTRICAL CHARACTERISTIC (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		$I_{GES}$	$V_{GE} = \pm 20V, V_{CE} = 0$	_	_	±500	nA
Collector Cut-	Off Current	ICES	$V_{CE} = 600V, V_{GE} = 0$	1	_	1.0	mA
Gate-Emitter	Cut-off Voltage	V <sub>GE(OFF)</sub>	$I_{C}=80$ mA, $V_{CE}=5$ V	3.0	_	6.0	V
Collector-Emitter Saturation		$V_{\text{CE(sat)}}(1)$	$I_{C} = 10A, V_{GE} = 15V$	I	_	2.0	V
Voltage		V <sub>CE(sat)</sub> (2)	$I_{C} = 80A, V_{GE} = 15V$		2.5	3.5	
Input Capacitance		Cies	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	-	5500	_	pF
Switching Time	Rise Time	t <sub>r</sub>	VOUT 15V 0 VIN 33Ω Σ 0 VCC=300V	_	0.3	0.6	- - μs
	Turn-on Time	t <sub>on</sub>			0.5	0.8	
	Fall Time	tf			0.25	0.40	
	Turn-off Time	t <sub>off</sub>			0.7	1.0	
Thermal Resistance		$ m R_{th(j-c)}$		_	_	0.625	°C/W

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